

## Low Voltage CMOS Driver Circuit

### Description

The e5130 contains 4 independent driver outputs with an ON resistance of typ. 25  $\Omega$  (15  $\Omega$ ) tor the P-channel output transistors and typ. 20  $\Omega$  (13  $\Omega$ ) for the N-channel output transistors; at a supply voltage of 1.5 V (3 V). To obtain a fast transition of the outputs, even for slow rise/-fall time input signals, all digital inputs (IN1 ... IN4) have a schmitt-trigger characteristic; with a hysteresis of

### **Features**

- 1.1 3.6 V operating voltage range
- 4 non-inverting, tristatable drivers for the following applications:
- Motor driver for bipolar stepper motors in watch/clock applications
- Driver for piezoelectric transducers (buzzer)
- LED Driver

TRI

**Pad Configuration** 

Line driver for medium speed applications

typ. 50 mV. If a higher driving capability is needed, all inputs and outputs may be connected in parallel. In this case the rise/-fall time of the input signals IN1 ... IN4 must be less than 200 nsec. Due to the fast switching characteristic of the tristatable output drivers, the circuit is also suited as low voltage bus driver.

### Advantages

- High load current at low supply voltage
- Replaces several discrete transistors
- Tri-state operation possible
- Possible applications:
- Motor driver
- Radio controlled clock/watch
- Line driver for mini-computer, laptop

- LED driver
- Relay driver

# OUT1 OUT2 OUT3 $V_{DD}$

e5130

IN3

IN4

VSS

DUT4	Name	Description
	V <sub>DD</sub>	Positive supply voltage
	V <sub>SS</sub>	Negative supply voltage
	IN1 IN4	Digital inputs
	TRI	Tristate input
	OUT1 OUT4	Drive outputs
	Chipsize: $x = 1.08$ m	y = 1.42  mm

Chipsize: x = 1.08 mm, y = 1.42 mm,Padwindow: 90 x 90 µ

### **Ordering Information**

IN1

IN2

Extended Type Number	Package	Remarks		
e5130A-DIT	Die	Die in Trays		



## **Absolute Maximum Ratings**

Absolute maximum ratings define parameter limits which, it exceeded, may permanently change or damage the device. All inputs and outputs on circuits are highly protected against electrostatic discharges.

However, precautions to minimize build-up of electrostatic charges during handling are recommended.

The circuits are protected against supply voltage reversal for typically 5 minutes, if the current is limited to 120 mA.

Parameters	Symbol	Value	Unit
Supply voltage	$V_{DD}-V_{SS} \\$	-0.3 to $+5$	V
Input voltage range, all inputs	VI	$V_{SS} - 0.3$ to $V_{DD} + 0.3$	V
Operating ambient temperature range		- 20 to + 70	°C
Storage temperature range		- 40 to + 125	°C
Lead temperature during soldering at 2 mm distance, 10 s		260	°C

## **Operating Characteristics**

 $V_{SS} = 0$  V,  $V_{DD} = +1.5$  V,  $T_{amb} = +25$  °C, unless otherwise specified. All voltage levels are measured with reference to  $V_{SS}$ .

Parameters	Test Conditions / Pin	Symbol	Min	Тур	Max	Unit		
Operating voltage		V <sub>DD</sub>	1.1		3.6	V		
Operating temperature		T <sub>amb</sub>	- 10		60	°C		
Operating current (standby)	$V_{DD} = 3.6 \text{ V}, R_{L12} = R_{L34} = \infty,$ IN1 to IN4 at V <sub>DD</sub> or V <sub>SS</sub> , TRI at V <sub>SS</sub>	I <sub>DD</sub>		0.05	1	μΑ		
Drive output OUT1 to OUT4								
Output current	$V_{DD} = 1.2 \text{ V}, R_{L12} = R_{L34} = 200 \Omega$	I <sub>OUT</sub>	± 4.3	± 4.75		mA		
Output current	$V_{DD} = 1.5 \text{ V}, R_{L12} = R_{L34} = 200 \ \Omega$	I <sub>OUT</sub>	± 5.7	± 6.20		mA		
Output current	$V_{DD} = 3.0 \text{ V}, R_{L12} = R_{L34} = 200 \Omega$	I <sub>OUT</sub>	± 12	± 13		mA		
Delay time	$V_{DD} = 3 V, C_L = 50 pF$	T <sub>Dr</sub> , T <sub>Df</sub>		35	60	ns		
Delay time	$V_{DD} = 1.5 \text{ V}, C_L = 50 \text{ pF},$ see figure 2, note 1	T <sub>Dr</sub> , T <sub>Df</sub>		80	150	ns		
Rise/-fall time	$V_{DD} = 3 V, C_L = 50 pF$	t <sub>r</sub> , t <sub>f</sub>		8	15	ns		
Rise/-fall time	$V_{DD} = 1.5 V, C_L = 50 pF,$ see figure 2, note 2	t <sub>r</sub> , t <sub>f</sub>		12	25	ns		
Digital input IN1 to IN4								
Input current	$V_{IL} = 0 V$	I <sub>IL</sub>			-100	nA		
Input current	$V_{IH} = V_{DD}$	I <sub>IH</sub>			100	nA		
Threshold	V	V <sub>TH</sub>		$V_{DD}/2$		V		
Hysteresis	mV	V <sub>HYST</sub>		50		mV		
Tristate input TRI								
Input current TRI	$V_{IH} = V_{DD}$	I <sub>IH</sub>	0.15	0.4	1.2	μΑ		









Figure 3. Typical current into 200  $\Omega$  load resistor, condition as per figure 1



Figure 4. Typical output on-resistance vs. supply voltage at  $V_{DS} = 0.2 \text{ V}$ 



Figure 5. Pad coordinates



### **Application Circuit**



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Data sheets can also be retrieved from the Internet: http://www.atmel-wm.com

Atmel Germany GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany Telephone: 49 (0)7131 67 2594, Fax number: 49 (0)7131 67 2423